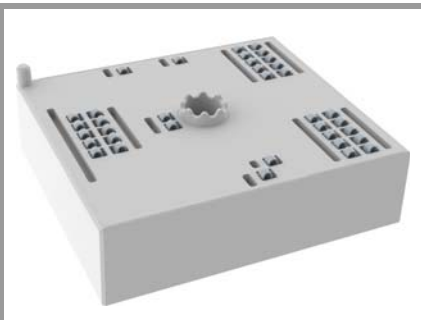


SKiiP 22GB17E4V1



MiniSKiiP® 2 Dual

Half-Bridge

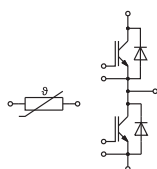
SKiiP 22GB17E4V1

Features*

- Trench IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised: File no. E63532
- NTC T-Sensor

Remarks

- Max. case temperature limited to $T_C=125^\circ\text{C}$
- Product reliability results valid for $T_j \leq 150^\circ\text{C}$ (recommended $T_{j,op} = -40 \dots +150^\circ\text{C}$)
- The creepage distance between T-Sensor and ground is 8mm

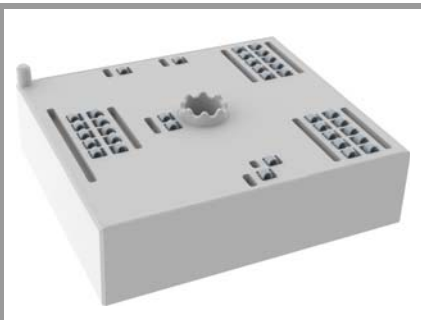


GB

| Absolute Maximum Ratings | | | | |
|--------------------------|---|---------------------------|------------------|---------------|
| Symbol | Conditions | Values | Unit | |
| Inverter - IGBT | | | | |
| V_{CES} | $T_j = 25^\circ\text{C}$ | 1700 | V | |
| I_C | $T_j = 175^\circ\text{C}$ | $T_s = 25^\circ\text{C}$ | 117 | A |
| | | $T_s = 70^\circ\text{C}$ | 95 | A |
| I_{Cnom} | | 100 | A | |
| I_{CRM} | | 300 | A | |
| V_{GES} | | -20 ... 20 | V | |
| t_{psc} | $V_{CC} = 1000\text{ V}$ $V_{GE} \leq 15\text{ V}$ $V_{CES} \leq 1700\text{ V}$ | $T_j = 150^\circ\text{C}$ | 10 | μs |
| T_j | | -40 ... 175 | $^\circ\text{C}$ | |
| Inverse - Diode | | | | |
| I_F | $T_j = 175^\circ\text{C}$ | $T_s = 25^\circ\text{C}$ | 91 | A |
| | | $T_s = 70^\circ\text{C}$ | 71 | A |
| I_{FRM} | | 200 | A | |
| I_{FSM} | 10 ms, sin 180°, $T_j = 150^\circ\text{C}$ | 580 | A | |
| T_j | | -40 ... 175 | $^\circ\text{C}$ | |
| Module | | | | |
| $I_{t(RMS)}$ | $T_{terminal} = 80^\circ\text{C}$, 20 A per spring | 200 | A | |
| T_{stg} | module without TIM | -40 ... 125 | $^\circ\text{C}$ | |
| V_{isol} | AC sinus 50 Hz, $t = 1\text{ min}$ | 2500 | V | |

| Characteristics | | | | | |
|------------------------|---|---------------------------|------|------|------------|
| Symbol | Conditions | min. | typ. | max. | Unit |
| Inverter - IGBT | | | | | |
| $V_{CE(sat)}$ | $I_C = 100\text{ A}$ $V_{GE} = 15\text{ V}$ chipelevel | $T_j = 25^\circ\text{C}$ | 1.90 | 2.20 | V |
| | | $T_j = 150^\circ\text{C}$ | 2.30 | 2.60 | V |
| V_{CE0} | chipelevel | $T_j = 25^\circ\text{C}$ | 0.80 | 0.90 | V |
| | | $T_j = 150^\circ\text{C}$ | 0.70 | 0.80 | V |
| r_{CE} | $V_{GE} = 15\text{ V}$ chipelevel | $T_j = 25^\circ\text{C}$ | 11 | 13 | m Ω |
| | | $T_j = 150^\circ\text{C}$ | 16 | 18 | m Ω |
| $V_{GE(th)}$ | $V_{GE} = V_{CE}$, $I_C = 4\text{ mA}$ | 5.2 | 5.8 | 6.4 | V |
| I_{CES} | $V_{GE} = 0\text{ V}$ $V_{CE} = 1700\text{ V}$ | $T_j = 25^\circ\text{C}$ | | 0.3 | mA |
| | | | | | mA |
| C_{ies} | $V_{CE} = 25\text{ V}$ | | 8.00 | | nF |
| C_{oes} | $V_{GE} = 0\text{ V}$ | | 0.34 | | nF |
| C_{res} | | | 0.29 | | nF |
| Q_G | -8 V...+15 V | | 800 | | nC |
| R_{Gint} | $T_j = 25^\circ\text{C}$ | | 7.5 | | Ω |
| $t_{d(on)}$ | $V_{CC} = 900\text{ V}$ $I_C = 100\text{ A}$ | | 232 | | ns |
| t_r | $R_{G on} = 2\ \Omega$ | | 41 | | ns |
| E_{on} | $R_{G off} = 2\ \Omega$ | | 22.2 | | mJ |
| $t_{d(off)}$ | $di/dt_{on} = 2892\text{ A}/\mu\text{s}$ | | 600 | | ns |
| t_f | $di/dt_{off} = 665\text{ A}/\mu\text{s}$ $dv/dt = 5490\text{ V}/\mu\text{s}$ | | 144 | | ns |
| E_{off} | $V_{GE} = +15/-15\text{ V}$ $L_s = 25\text{ nH}$ | | 30.7 | | mJ |
| $R_{th(j-s)}$ | per IGBT, $\lambda_{paste} = 0.8\text{ W}/(\text{K}\cdot\text{m})$ | | 0.43 | | K/W |

SKiiP 22GB17E4V1



MiniSKiiP® 2 Dual

Half-Bridge

SKiiP 22GB17E4V1

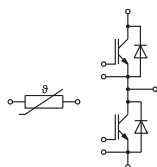
Features*

- Trench IGBTs
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- Highly reliable spring contacts for electrical connections
- UL recognised: File no. E63532
- NTC T-Sensor

Remarks

- Max. case temperature limited to $T_C=125^\circ\text{C}$
- Product reliability results valid for $T_j \leq 150^\circ\text{C}$ (recommended $T_{j,op} = -40 \dots +150^\circ\text{C}$)
- The creepage distance between T-Sensor and ground is 8mm

| Characteristics | | | | | | |
|---------------------------|--|---------------------------|------|---------------|------|---------------|
| Symbol | Conditions | | min. | typ. | max. | Unit |
| Inverse - Diode | | | | | | |
| $V_F = V_{EC}$ | $I_F = 100 \text{ A}$ $V_{GE} = 0 \text{ V}$ chipelevel | $T_j = 25^\circ\text{C}$ | | 2.00 | 2.40 | V |
| | | $T_j = 150^\circ\text{C}$ | | 2.15 | 2.57 | V |
| V_{F0} | chipelevel | $T_j = 25^\circ\text{C}$ | | 1.32 | 1.56 | V |
| | | $T_j = 150^\circ\text{C}$ | | 1.08 | 1.22 | V |
| r_F | chipelevel | $T_j = 25^\circ\text{C}$ | | 6.8 | 8.4 | m Ω |
| | | $T_j = 150^\circ\text{C}$ | | 11 | 14 | m Ω |
| I_{RRM} | $I_F = 100 \text{ A}$ | | | 165 | | A |
| Q_{rr} | $di/dt_{off} = 3753 \text{ A}/\mu\text{s}$ | | | 32.5 | | μC |
| E_{rr} | $V_{GE} = -15 \text{ V}$ $V_{CC} = 900 \text{ V}$ | | | 20.9 | | mJ |
| $R_{th(j-s)}$ | per Diode, $\lambda_{paste}=0.8 \text{ W}/(\text{K}\cdot\text{m})$ | | | 0.7 | | K/W |
| Module | | | | | | |
| L_{CE} | | | | 20 | | nH |
| M_s | to heat sink | | 2 | | 2.5 | Nm |
| w | | | | 50 | | g |
| Temperature Sensor | | | | | | |
| R_{100} | $T_c=100^\circ\text{C}$ ($R_{25}=5 \text{ k}\Omega$) | | | $493 \pm 5\%$ | | Ω |
| $B_{25/85}$ | $R_{(T)}=R_{25} \cdot \exp[B_{25/85} \cdot (1/T - 1/298)]$, T[K] | | | 3420 | | K |



GB

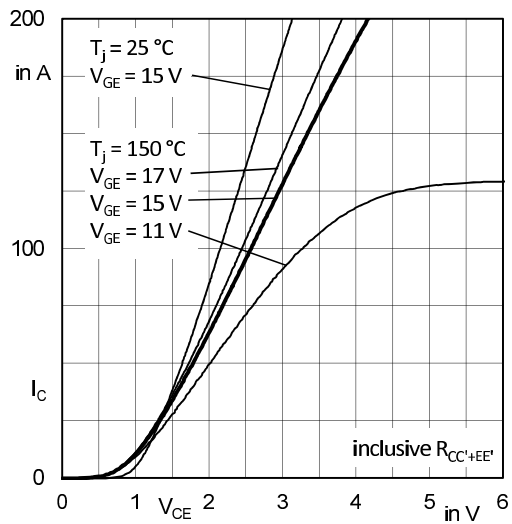


Fig. 1: Typ. output characteristic

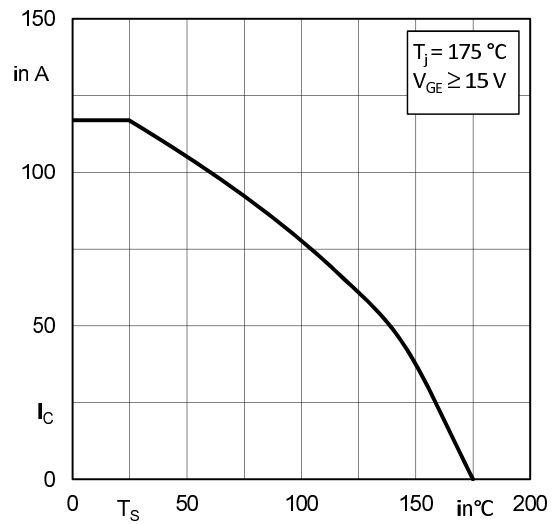


Fig. 2: Rated current vs. temperature $I_C = f(T_S)$

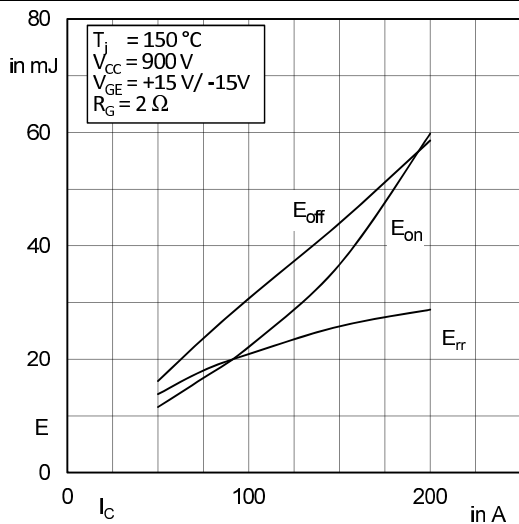


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

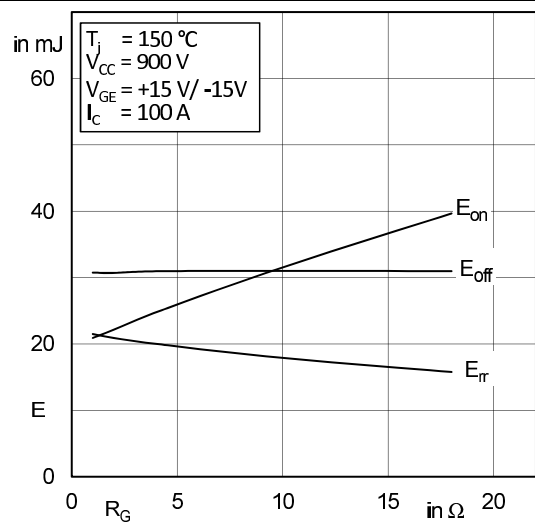


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

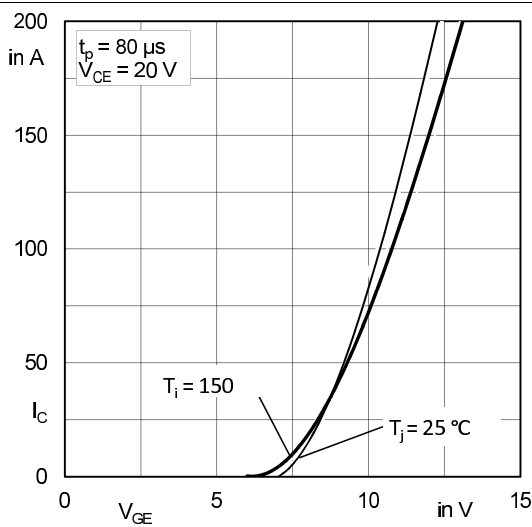


Fig. 5: Typ. transfer characteristic

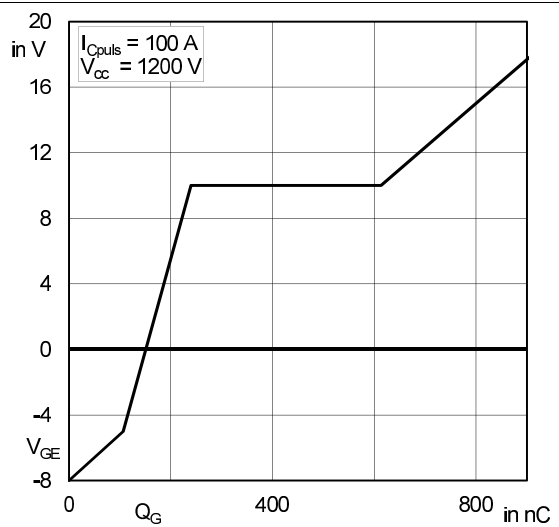


Fig. 6: Typ. gate charge characteristic

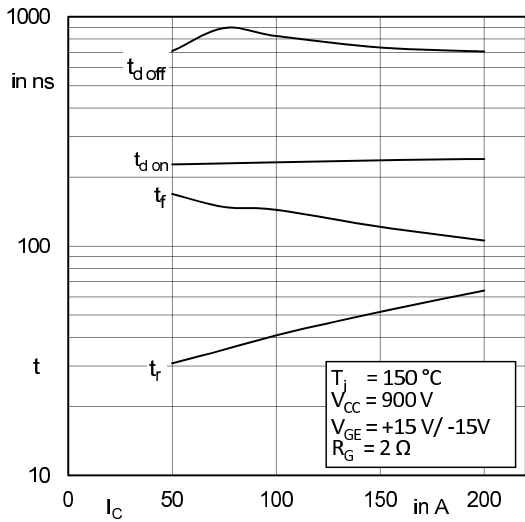


Fig. 7: Typ. switching times vs. I_C

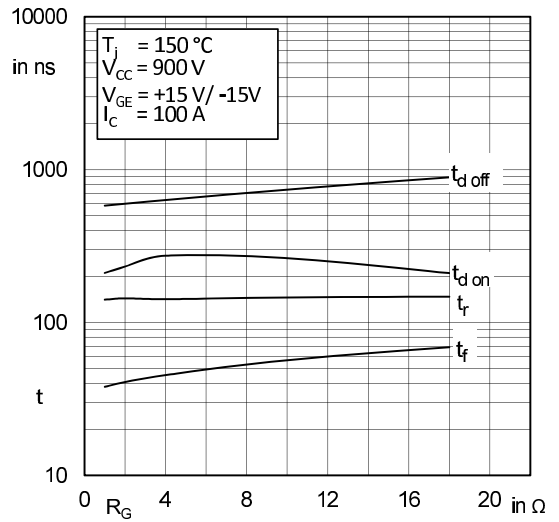


Fig. 8: Typ. switching times vs. gate resistor R_G

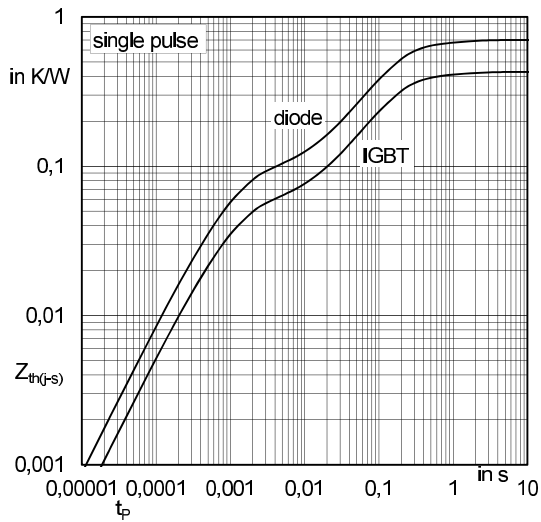


Fig. 9: Typ. transient thermal impedance

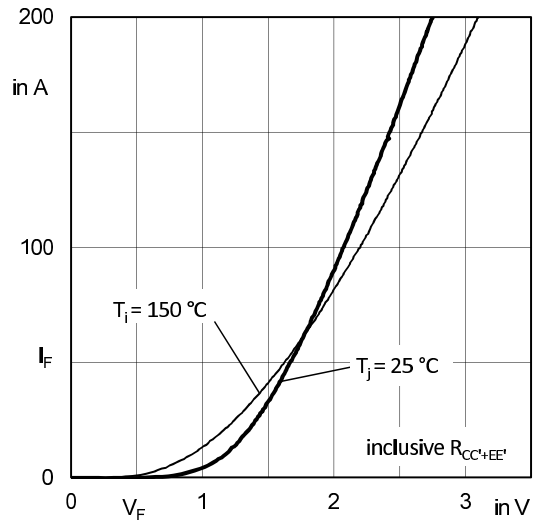


Fig. 10: Typ. CAL diode forward characteristic

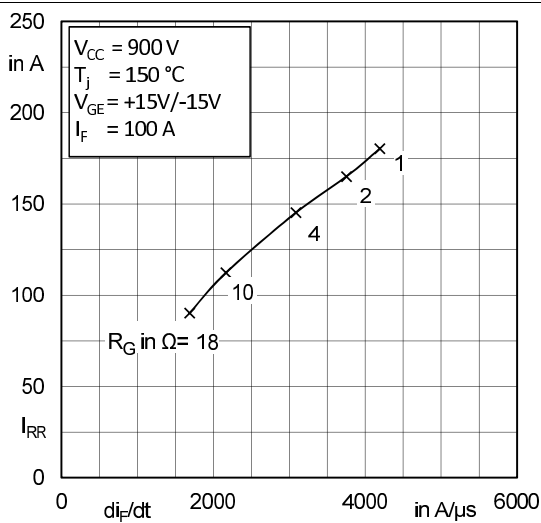


Fig. 11: Typ. CAL diode peak reverse recovery current

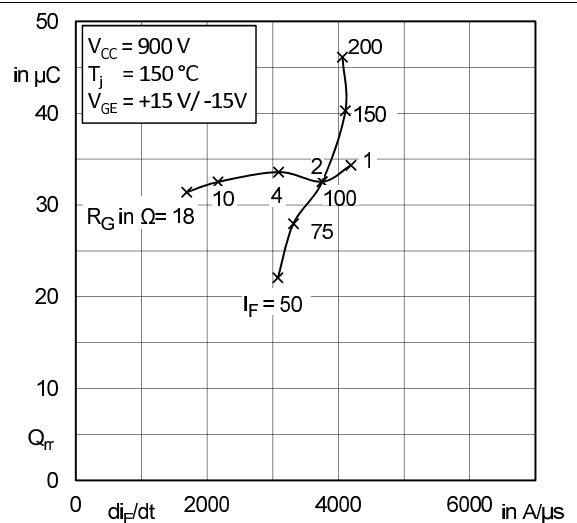
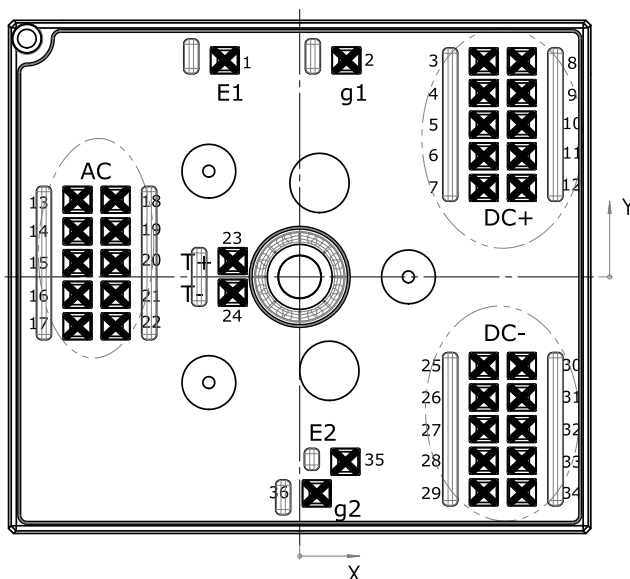


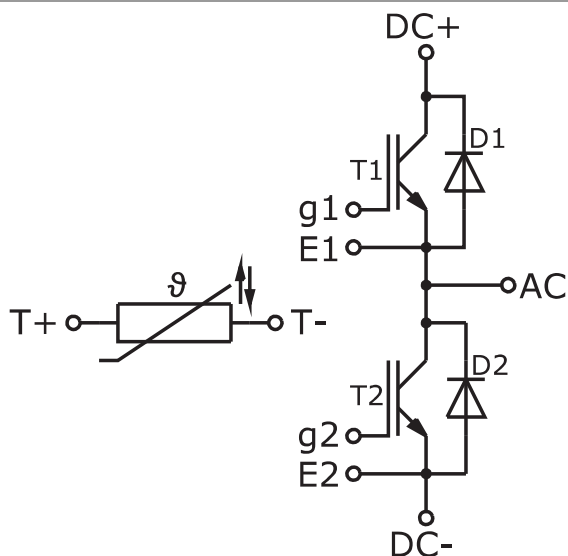
Fig. 12: Typ. CAL diode recovery charge

| Pin out | | | | | | | |
|---------|--------|------|----------|-----|--------|-------|----------|
| Pin | X | Y | Function | Pin | X | Y | Function |
| 1 | -7,58 | 21,9 | E1 | 19 | -18,63 | 4,6 | AC |
| 2 | 4,73 | 21,9 | g1 | 20 | -18,63 | 1,4 | AC |
| 3 | 18,63 | 21,8 | DC+ | 21 | -18,63 | -1,8 | AC |
| 4 | 18,63 | 18,6 | DC+ | 22 | -18,63 | -5 | AC |
| 5 | 18,63 | 15,4 | DC+ | 23 | -6,78 | 1,6 | T+ |
| 6 | 18,63 | 12,2 | DC+ | 24 | -6,78 | -1,6 | T- |
| 7 | 18,63 | 9 | DC+ | 25 | 18,63 | -9 | DC- |
| 8 | 22,48 | 21,8 | DC+ | 26 | 18,63 | -12,2 | DC- |
| 9 | 22,48 | 18,6 | DC+ | 27 | 18,63 | -15,4 | DC- |
| 10 | 22,48 | 15,4 | DC+ | 28 | 18,63 | -18,6 | DC- |
| 11 | 22,48 | 12,2 | DC+ | 29 | 18,63 | -21,8 | DC- |
| 12 | 22,48 | 9 | DC+ | 30 | 22,48 | -9 | DC- |
| 13 | -22,48 | 7,8 | AC | 31 | 22,48 | -12,2 | DC- |
| 14 | -22,48 | 4,6 | AC | 32 | 22,48 | -15,4 | DC- |
| 15 | -22,48 | 1,4 | AC | 33 | 22,48 | -18,6 | DC- |
| 16 | -22,48 | -1,8 | AC | 34 | 22,48 | -21,8 | DC- |
| 17 | -22,48 | -5 | AC | 35 | 4,63 | -18,7 | E2 |
| 18 | -18,63 | 7,8 | AC | 36 | 1,73 | -21,9 | g2 |

all values in [mm]



Pinout and Dimensions



Pinout

This is an electrostatic discharge sensitive device (ESDS) due to international standard IEC 61340.

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